



**Features:**

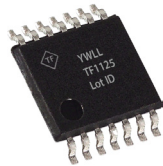
- Floating high-side driver in bootstrap operation to 200V
- 1.2A/5A (TF1125), 0.8A/3.3A (TF1123), 0.4/1.67A (TF1121) peak source/sink current
- 0.4Ω/2Ω pull down/pull up impedance
- Independent high-side and low-side logic inputs
- High speed gate drivers at 5V supply
- Proprietary bootstrap capacitor auto-recharge technology
- Fast propagation delays (25ns typical)
- Separate source and sink outputs

**Applications**

- High Speed DC-DC Converters
- High frequency Power Supplies
- Wireless Charging



TDFN-10



eTSSOP-14

**Description**

The TF1125/1123/1121 are high-side/low-side gate drivers with 5V supply giving the ability to drive logic level MOSFETs. The high-side driver features a floating supply for operation to 200V.

The three parts, TF1125/1123/1121, differ by output source/sink current (1.2A/5A, 0.8A/3.3A, 0.4A/1.67A respectively). For all the devices, a high sink capability maintains the gate drive line at a low level during high dv/dt prohibiting unintended turn on of the MOSFET.

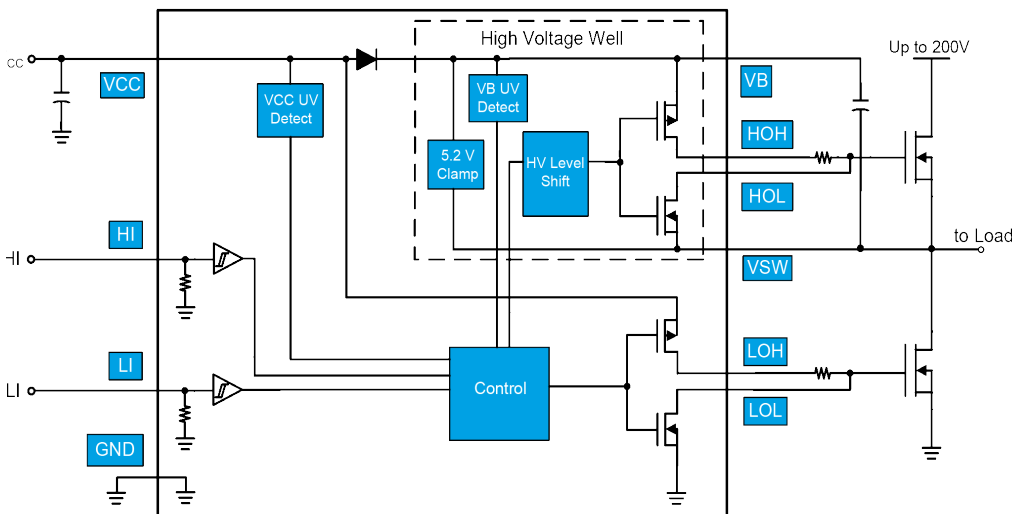
Ultra fast propagation delays and rise/fall times with a proprietary bootstrap capacitor auto-recharge allow high frequency operation with smaller component footprints; and with the integrated bootstrap diode, and the small TDFN-10 and TSSOP-14 package, the required area compared to a discrete solution is greatly reduced.

**Ordering Information**

Year Week LLot ID

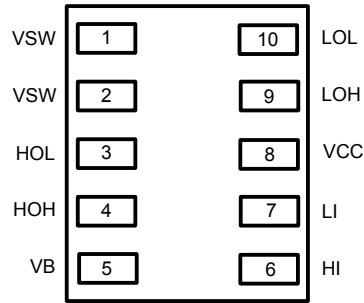
PART NUMBER	PACKAGE	PACKING / Qty	MARK
TF1125/1123/1121-NBP	TDFN-10	T & R / 3,000	YWLL PART#
TF1125/1123/1121-6BG	eTSSOP-14	T & R / 1,000	YWLL TF11XX Lot ID

**Typical Application**

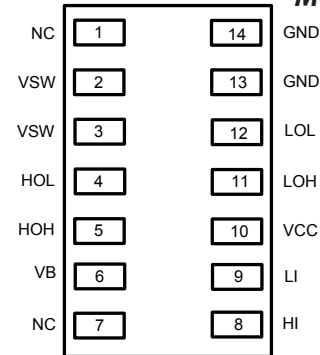


## Pin Diagrams

### 200V High Speed Logic Level MOSFET Gate Driver



**Top View: TDFN-10**



**Top View: eTSSOP-14**

TF1125/1123/1121

## Pin Descriptions

PIN NAME	PIN DESCRIPTION
VSW	High-side bootstrap return
HOL	High-side gate driver sink output
HOH	High-side gate driver source output
VB	High-side bootstrap supply
HI	High-side gate driver control input
LI	Low-side gate driver control input
VCC	Low-side gate driver supply and control supply
LOH	Low-side gate driver source output
LOL	Low-side gate driver sink output
GND	Low-side and control ground, PAD for both packages

**200V High Speed Logic Level  
MOSFET Gate Driver**
**Absolute Maximum Ratings (NOTE1)**

$V_B$  - High side floating supply voltage.....-0.3V to +207V  
 $V_S$  - High side floating supply offset voltage..... $V_B-7V$  to  $V_B+0.3V$   
 $V_{HO}$  - High side floating output voltage..... $V_S-0.3V$  to  $V_B+0.3V$   
 $dV_S/dt$  - Offset supply voltage transient.....50 V/ns

$V_{CC}$  - Logic & low side fixed supply voltage.....-0.3V to +7V  
 $V_{LO}$  - Low side output voltage.....-0.3V to  $V_{CC}+0.3V$

$V_{IN}$  - Logic input voltage (HI and LI).....-0.3V to +7V

$P_D$  - Package power dissipation at  $T_A \leq 25^\circ\text{C}$   
 TDFN-10.....TBD  
 eTSSOP-14.....TBD

**NOTE1** Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TDFN-10 Thermal Resistance (**NOTE2**)

$\theta_{JA}$ .....TBD °C/W

eTSSOP-14 Thermal Resistance (**NOTE2**)

$\theta_{JA}$ .....TBD °C/W

$T_J$  - Junction operating temperature .....-40 °C to +150 °C

$T_L$  - Lead temperature (soldering, 10s) ..... +300 °C

$T_{stg}$  - Storage temperature range .....-55 °C to +150 °C

**NOTE2** When mounted on a standard JEDEC 2-layer FR-4 board.

**Recommended Operating Conditions (NOTE3)**

Symbol	Parameter	MIN	MAX	Unit
$V_B$	High side floating supply absolute voltage	$V_S + 4$	$V_S + 5.5$	V
$V_S$	High side floating supply offset voltage	-5	200	V
$V_{HO}$	High side floating output voltage	$V_S$	$V_B$	V
$V_{CC}$	Low side fixed supply voltage	4.5	5.5	V
$V_{LO}$	Low side output voltage	0	$V_{CC}$	V
$V_{IN}$	Logic input voltage (HI & LI)	0	5	V
$T_A$	Ambient temperature	-40	125	°C

**NOTE3** Voltage amplitudes referenced to GND.

## DC Electrical Characteristics

### 200V High Speed Logic Level MOSFET Gate Driver

$V_{CC} = V_{BS} = 5V$ ,  $T_A = 25^\circ C$  and  $V_{SW} = GND = 0V$ , and no load on LOL, LOH, HOL, and HOH, unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
$V_{CC}$	Supply Voltage		4.5	5.0	5.5	V
$V_{IH}$	Logic "1" input voltage		3.8			
$V_{IL}$	Logic "0" input voltage				1.2	
$I_{CCQ}$	Quiescent $V_{CC}$ supply current	LI = HI = 0V		50		$\mu A$
$I_{CCO}$	Operating $V_{CC}$ supply current	f = 500kHz		0.5		mA
$I_{BSQ}$	Quiescent $V_{BS}$ supply current	LI = HI = 0V		80		$\mu A$
$I_{BSO}$	Operating $V_{BS}$ supply current	f = 500kHz		1.0		mA
$I_{IHYS}$	Input Hysteresis			2.5		
$V_{CCUV+}$	$V_{CC}$ supply under-voltage positive going threshold			3.7		V
$V_{CCUV-}$	$V_{CC}$ supply under-voltage negative going threshold			3.5		
$V_{BSUV+}$	$V_{BS}$ supply under-voltage positive going threshold			3.7		
$V_{BSUV-}$	$V_{BS}$ supply under-voltage negative going threshold			3.5		
$V_{BSClamp}$	Bootstrap supply clamp		4.7	5.2	5.5	
$V_{DL}$	Bootstrap diode low-current forward voltage	$I_{VCC-VB} = 100\mu A$		0.6		
$V_{DH}$	Bootstrap diode hi-current forward voltage	$I_{VCC-VB} = 100mA$		0.9		
$V_{DB}$	Bootstrap diode breakdown voltage		200			
$V_{OH}$	High-Level Output Voltage	$I_{OH} = 100mA$		0.2		
$V_{OL}$	Low-Level Output Voltage	$I_{OL} = 100mA$		0.06		
$I_{OH}$	Peak source current	TF1125		1.2		A
		TF1123		0.8		
		TF1121		0.4		
$I_{OL}$	Peak sink current	TF1125		5.0		A
		TF1123		3.3		
		TF1121		1.67		
$I_{OHLK}$	High-level output leakage current	HOH = LOH = 0V		1.5		$\mu A$
$I_{OLLK}$	Low-level output leakage current	HOL = LOL = 5V		1.5		$\mu A$

## AC Electrical Characteristics

### 200V High Speed Logic Level MOSFET Gate Driver

$V_{CC} = V_{BS} = 5V$ ,  $T_A = 25^\circ C$  and  $V_{SW} = GND = 0V$ , and no load on LOL, LOH, HOL, and HOH, unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
$t_{ONL}$	LO turn-on propagation delay	LI rising to LOH rising		25		ns
$t_{OFFL}$	LO turn-off propagation delay	LI falling to LOL falling		25		
$t_{ONH}$	HO turn-on propagation delay	HI rising to HOH rising		25		
$t_{OFFH}$	HO turn-off propagation delay	HI falling to HOL falling		25		
$t_{DM ON}$	Delay Matching: LO on & HO off			1.5		
$t_{DM OFF}$	Delay Matching: LO off & HO on			1.5		
$t_{HR}$	HO rise time (0.5V - 4.5V)	CL = 1000pF		7.0		
$t_{LR}$	LO rise time (0.5V - 4.5V)	CL = 1000pF		7.0		
$t_{HF}$	HO fall time (0.5V - 4.5V)	CL = 1000pF		1.5		
$t_{LF}$	LO fall time (0.5V - 4.5V)	CL = 1000pF		1.5		
$t_{PW}$	Minimum input pulse width that changes the output			10		
$t_{BS}$	Bootstrap diode reverse recovery time			40		

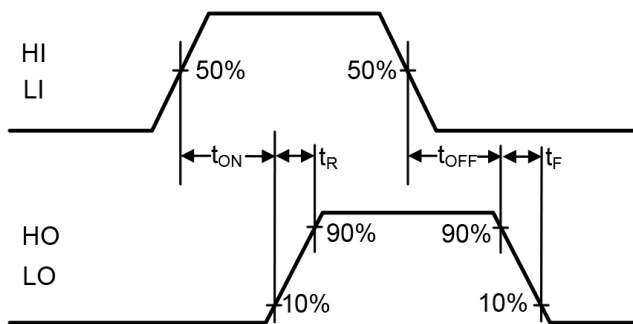


Figure 1. Switching Time Waveform Definitions

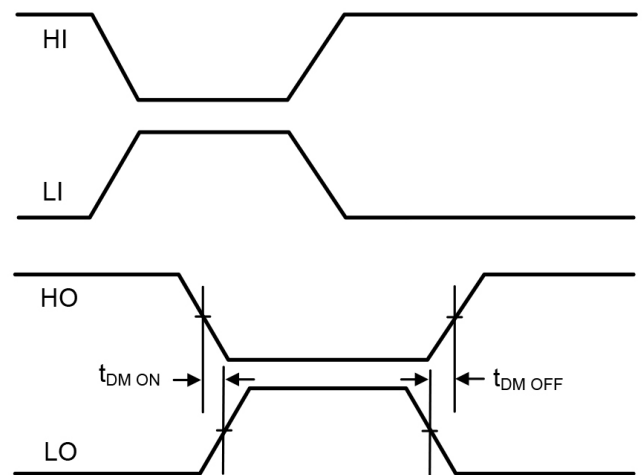


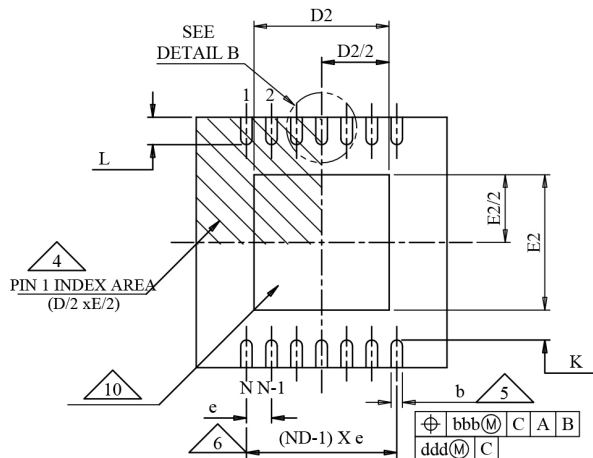
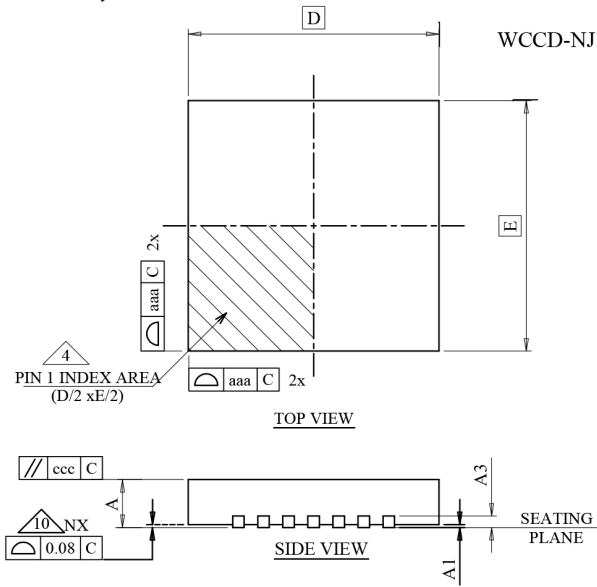
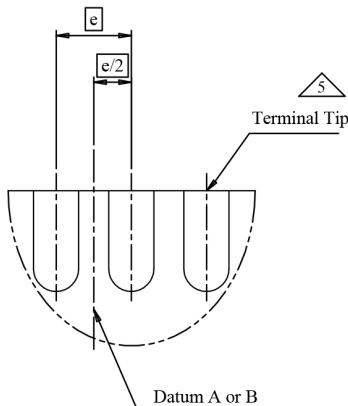
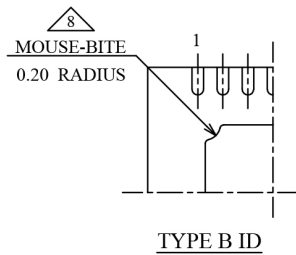
Figure 2. Delay Matching Waveform Definitions

# Package Dimensions (TDFN-10)

**200V High Speed Logic Level  
MOSFET Gate Driver**

Please contact support@tfsemi.com for package availability.

3x3mm, 10 pin, Pad Size: 1.8x2.5mm



**NOTES:**

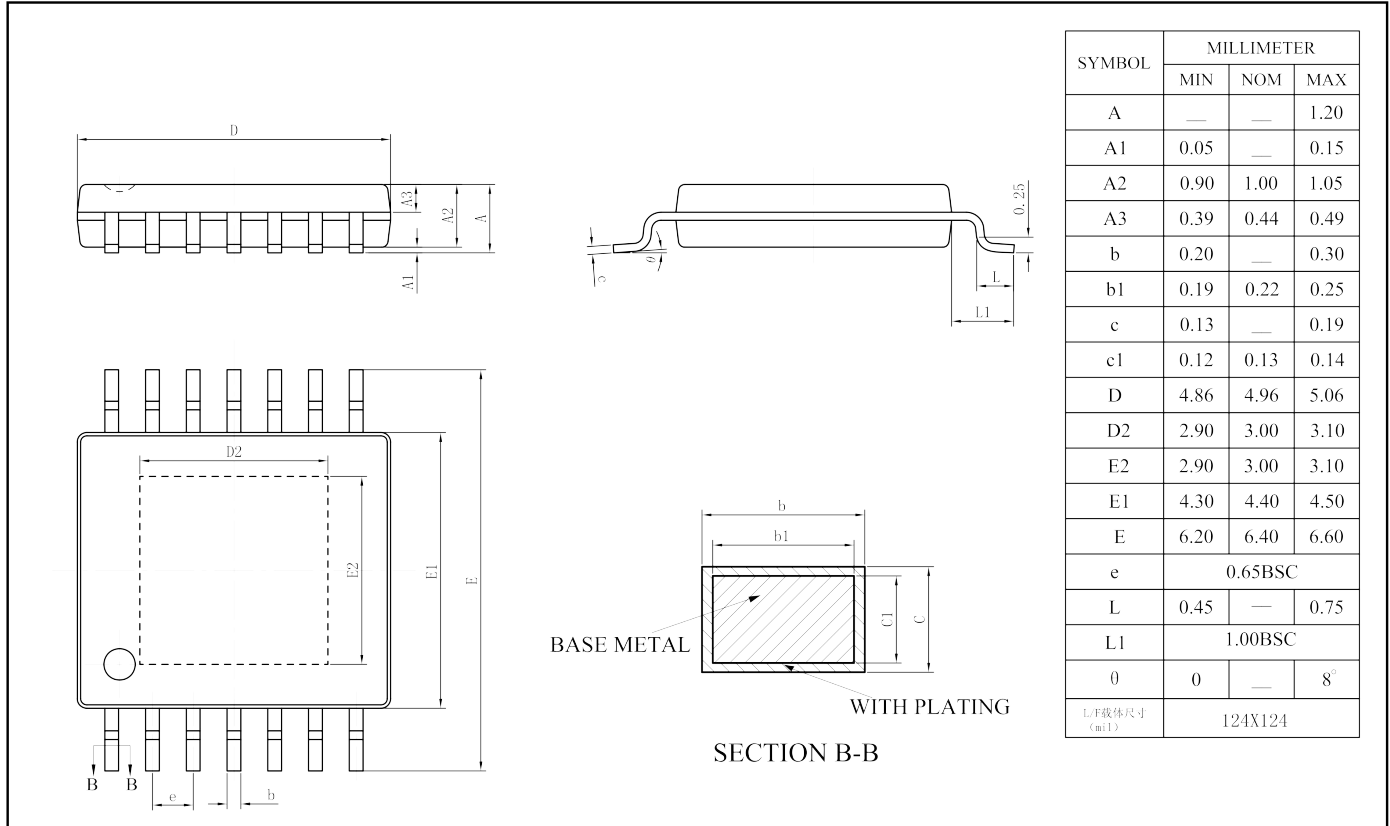
- Dimensions in table are the TF4601, WCCD-NJ1 variation of the MLP Dual Family Package Outline.
- Dimensioning and tolerancing conform to ASME Y14.5M-1994.
- All dimensions are in millimeters, angle is in degrees (°).
- N is the total number of terminals.
- The terminal #1 identifier and terminal numbering convention shall conform to JESD 95-1 SPP-012. Details of terminal #1 identifier are optional, but must be located within the zone indicated. The terminal #1 identifier may be either a mold, embedded metal or mark feature.
- Dimension b applies to metallized terminal and is measured between 0.15MM and 0.30MM from terminal tip.
- ND refers to the maximum number of terminals on D side.
- For a complete set of dimensions for each variation, see the individual variation and the common dimensions and tolerances on page 4.
- Unilateral coplanarity zone applies to the exposed heat sink slug as well as the terminals.
- In the case of the rectangular package, the terminal side of the package is determined as followed:
  - Type 1: The terminals are on the short side of the package.
  - Type 2: The terminals are on the long side of the package.
- Variation codes reference specific JEDEC MO-229 package variations. However, codes starting with NJR are not currently JEDEC registered and not defined in the 'Variation Designation' table. Variation with a star (\*) symbol are also not JEDEC registered.
- When more than one variation (option) exists for the same profile height, body size (DxE), and pitch then those variations will be denoted by an additional dash number (i.e. -1,-2, etc) designator to identify them. The new variations would be created from all or any of the following reasons :
  - Terminal count, Terminal length and/or exposed pad sizes.
- Variation with Exposed Tie Bars do not comply with JEDEC OUTLINE MO-229

Dimension	MIN	NOM	MAX	
A	Height	0.70	0.75	0.80
D	Length	2.0		
E	Width	2.0		
A1		0.00	0.02	0.05
A3		0.20 Ref		
e	Pitch	0.50		
K		0.20		
b	Lead Width	0.18	0.25	0.30
D2	DAP Length	1.55	1.70	1.80
E2	DAP Height	0.75	0.90	1.00
L		0.20	0.30	0.40

## Package Dimensions (eTSSOP-14)

**200V High Speed Logic Level  
MOSFET Gate Driver**

Please contact support@tfsemi.com for package availability.



## Notes

*200V High Speed Logic Level  
MOSFET Gate Driver*

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